

Electric Resistance Measurement System for Metals and Semiconductors TER series



Metal phase transformations, aging, recrystallization reactions

Capable of precise measurements of the electric resistance of metal alloys and semiconductors with the DC four-terminal method

Applications

- Research on metal phase transformation, age hardening, recrystallization
- Recrystallization analysis of amorphous metals
- Research and development of shape memory alloys
- Measurements of the electric resistance of various semiconductor materials at temperatures

Features

- Capable of electric resistance measurements in a constant-rate rising and falling temperature state and in a constant temperature state
- Capable of precise measurements with the DC four-terminal method
- Free from influence of thermal electromotive forces

Specifications

Electric Resistance Measurement System for Metals and Semiconductors TER series		
Type	TER-2000RH	TER-2000L
Measurement Properties and Measurement Method	Electric resistivity / DC four-terminal method	
Temperature Range	RT to 1200 °C	-150 °C to 200 °C
Measurement range	100Ω~5×10⁻⁵Ω	
Sample Size	φ 10 mm x 100 mm length	
Measurement Atmosphere	Inert gas flow, air, vacuum (optional)	
Optional	Cooling water circulator	